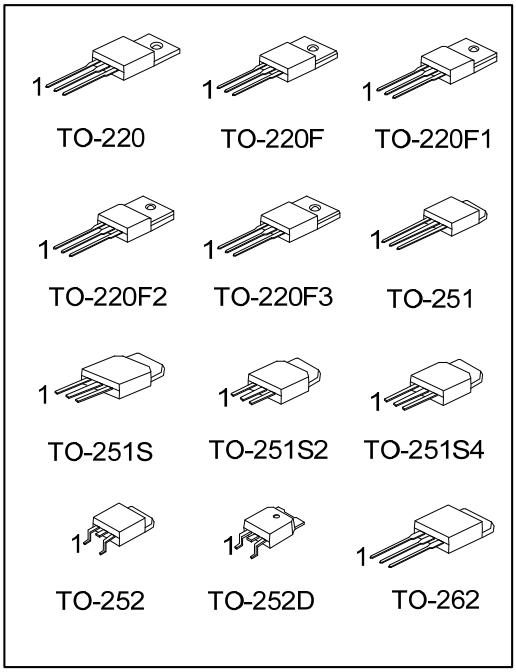
4N65K-MT

Power MOSFET

4.0A, 650V N-CHANNEL POWER MOSFET



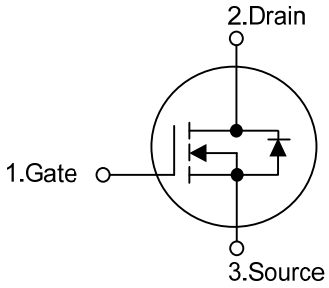
■ DESCRIPTION

The UTC **4N65K-MT** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristic. This power MOSFET is usually used in high speed switching applications including power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

* $R_{DS(ON)}$ < 2.5Ω @ V_{GS} = 10 V, I_D = 2.2 A
* Fast Switching Capability
* Avalanche Energy Specified
* Improved dv/dt Capability, High Ruggedness

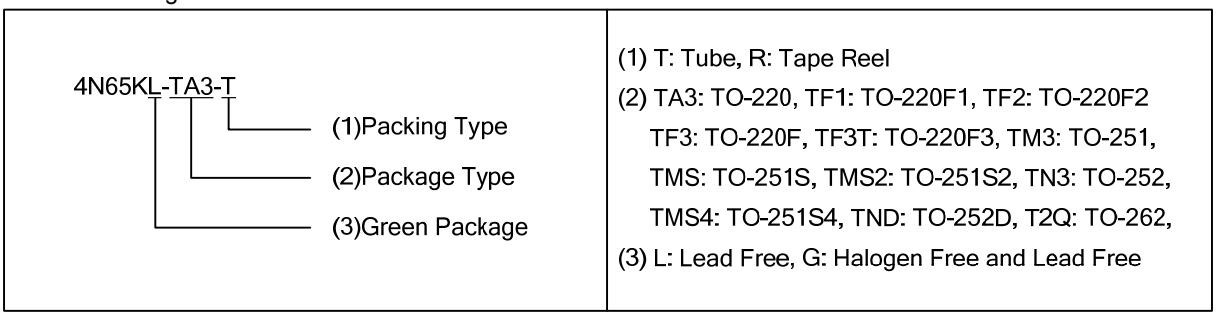
■ SYMBOL



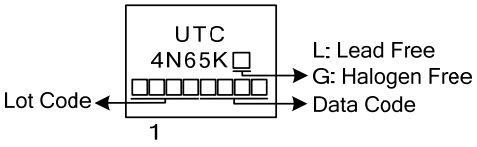
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N65KL-TA3-T	4N65KG-TA3-T	TO-220	G	D	S	Tube
4N65KL-TF3-T	4N65KG-TF3-T	TO-220F	G	D	S	Tube
4N65KL-TF1-T	4N65KG-TF1-T	TO-220F1	G	D	S	Tube
4N65KL-TF2-T	4N65KG-TF2-T	TO-220F2	G	D	S	Tube
4N65KL-TF3T-T	4N65KG-TF3T-T	TO-220F3	G	D	S	Tube
4N65KL-TM3-T	4N65KG-TM3-T	TO-251	G	D	S	Tube
4N65KL-TMS-T	4N65KG-TMS-T	TO-251S	G	D	S	Tube
4N65KL-TMS2-T	4N65KG-TMS2-T	TO-251S2	G	D	S	Tube
4N65KL-TMS4-T	4N65KG-TMS4-T	TO-251S4	G	D	S	Tube
4N65KL-TN3-R	4N65KG-TN3-R	TO-252	G	D	S	Tape Reel
4N65KL-TND-R	4N65KG-TND-R	TO-252D	G	D	S	Tape Reel
4N65KL-T2Q-T	4N65KG-T2Q-T	TO-262	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	4.0	A
	Pulsed (Note2)	I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note3)	E_{AS}	200	mJ
Peak Diode Recovery dv/dt (Note4)		dv/dt	2.63	V/ns
Power Dissipation	TO-220/TO-262	P_D	106	W
	TO-220F		34	W
	TO-220F1/TO-220F2 TO-220F3		36	W
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		50	W
Junction Temperature		T_J	+150	°C
Operating Temperature		T_{OPR}	-55 ~ +150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature
3. L=25mH, I_{AS}=4A, V_{DD}=50V, R_G=25 Ω, Starting T_J = 25°C
4. I_{SD}≤4.4A, di/dt≤200A/μs, V_{DD}≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL RESISTANCES CHARACTERISTICS

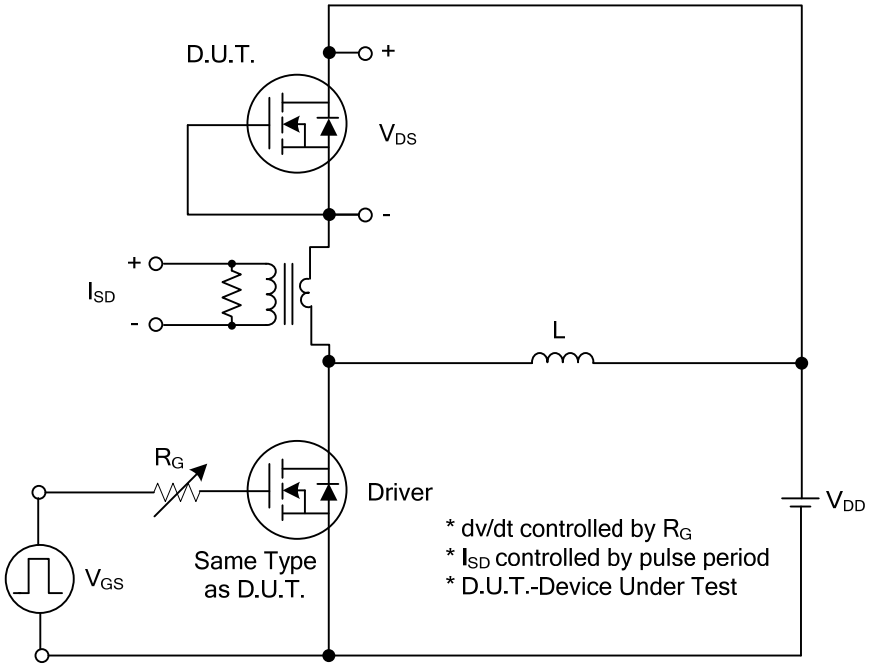
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-262 TO-220F/TO-220F1 TO-220F2/TO-220F3	θ_{JA}	62.5	°C/W
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		110	°C/W
Junction to Case	TO-220/TO-262	θ_{JC}	1.18	°C/W
	TO-220F/TO-220F1		3.47	°C/W
	TO-220F3		3.67	°C/W
	TO-220F2		3.57	°C/W
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		2.5	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C =25°C, unless otherwise specified)

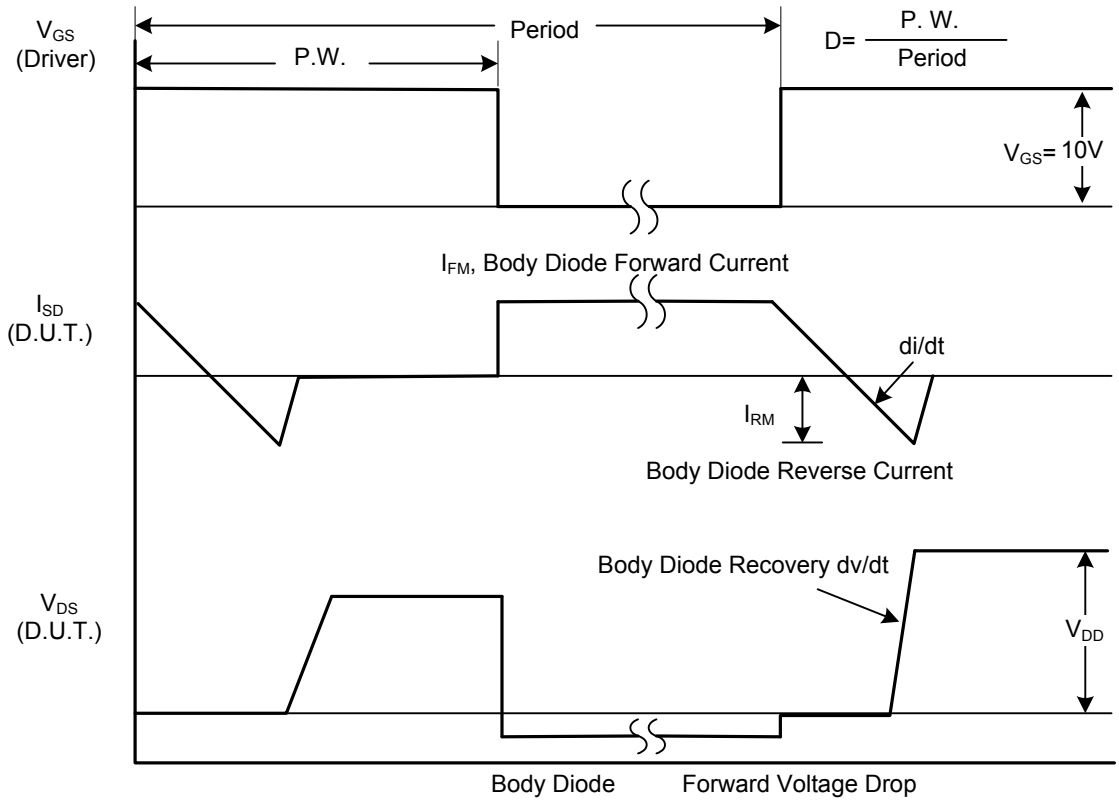
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0 V, I_D = 250μA	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 650 V, V_{GS} = 0 V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS} = 30 V, V_{DS} = 0 V			100	nA
	Reverse		V_{GS} = -30 V, V_{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D=250μA, Referenced to 25°C		0.6		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} = 10 V, I_D = 2.2A		1.77	2.50	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS} = 25 V, V_{GS} = 0V, f = 1MHz		430	750	pF
Output Capacitance		C_{OSS}			60	90	pF
Reverse Transfer Capacitance		C_{RSS}			6	11	pF
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q_G	V_{DS}=50V, V_{GS}=10V, I_D=1.3A, I_G=100μA (Note 1, 2)		17	20	nC
Gate-Source Charge		Q_{GS}			4.9	5.5	nC
Gate-Drain Charge		Q_{GD}			3.7	4.2	nC
Turn-On Delay Time		$t_{D(ON)}$	V_{DD} =30V, V_{GS}=10V, I_D =0.5A, R_G=25Ω (Note 1, 2)		44	60	ns
Turn-On Rise Time		t_R			50	100	ns
Turn-Off Delay Time		$t_{D(OFF)}$			80	130	ns
Turn-Off Fall Time		t_F			45	70	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				4.4	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				17.6	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S =4.4A, V_{GS} =0V			1.4	V
Body Diode Reverse Recovery Time		t_{rr}	I_S=4.4A, V_{GS}=0V, dI_F/dt=100A/μs (Note 1)		410		ns
Body Diode Reverse Recovery Charge		Q_{rr}			2.12		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle≤2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

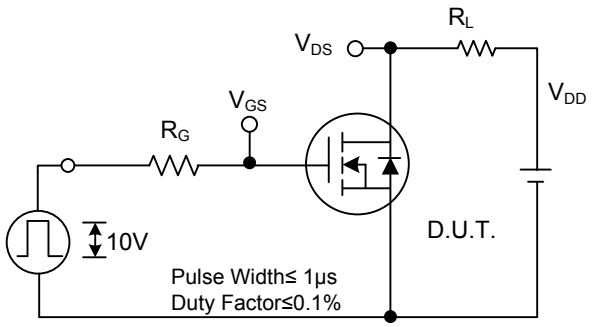


Peak Diode Recovery dv/dt Test Circuit

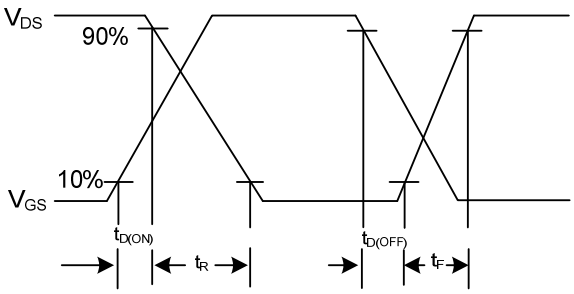


Peak Diode Recovery dv/dt Waveforms

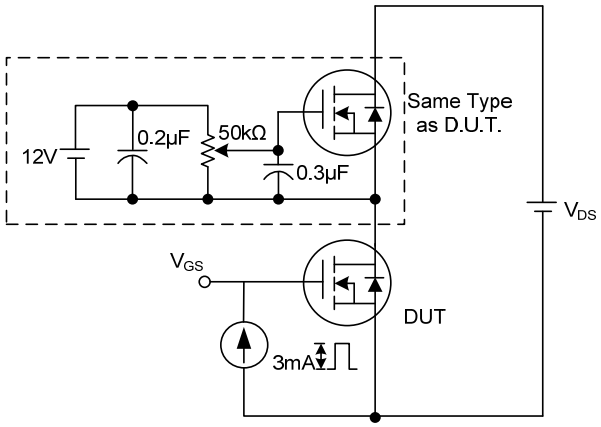
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



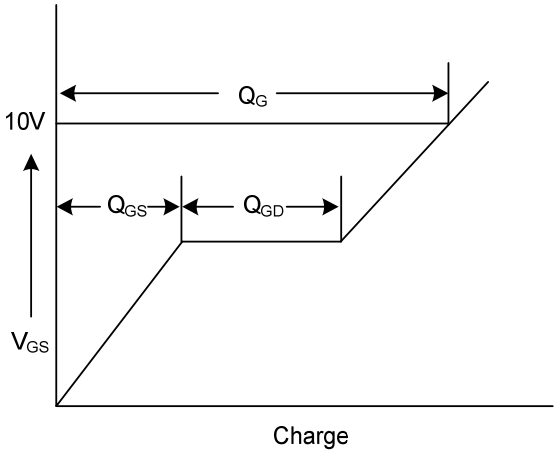
Switching Test Circuit



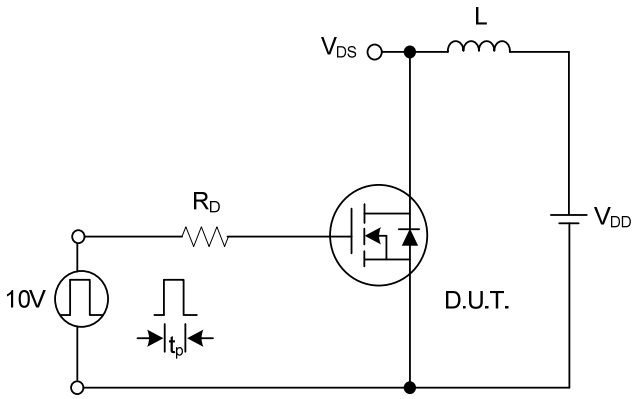
Switching Waveforms



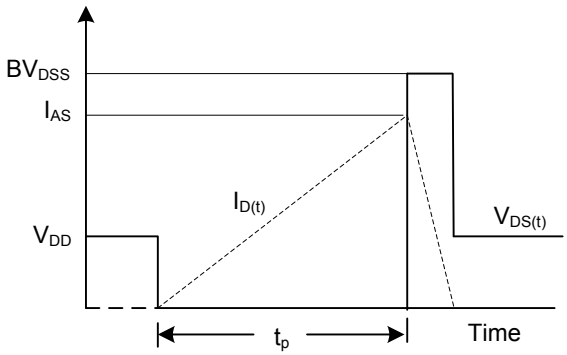
Gate Charge Test Circuit



Gate Charge Waveform

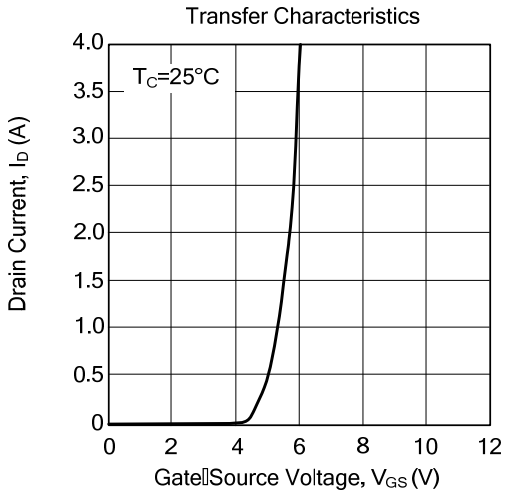


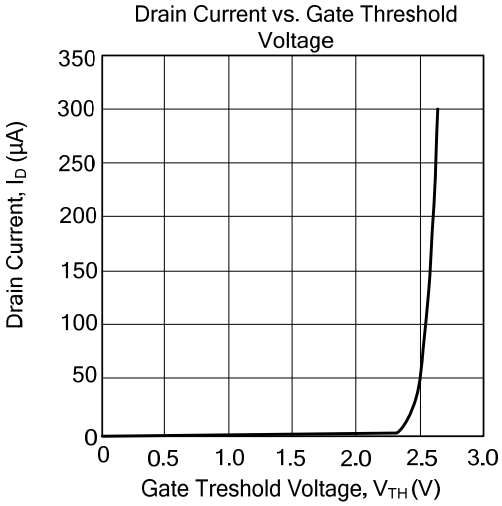
Unclamped Inductive Switching Test Circuit

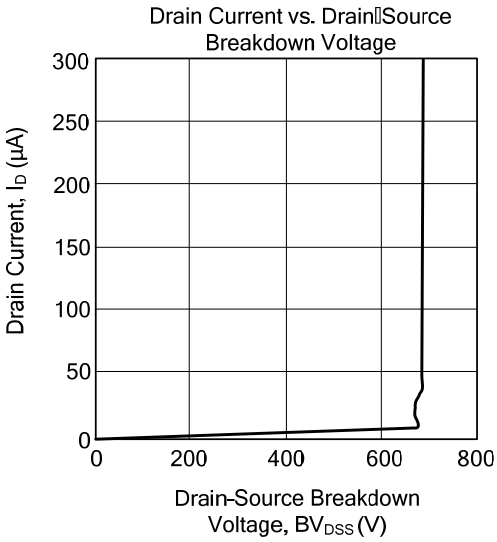


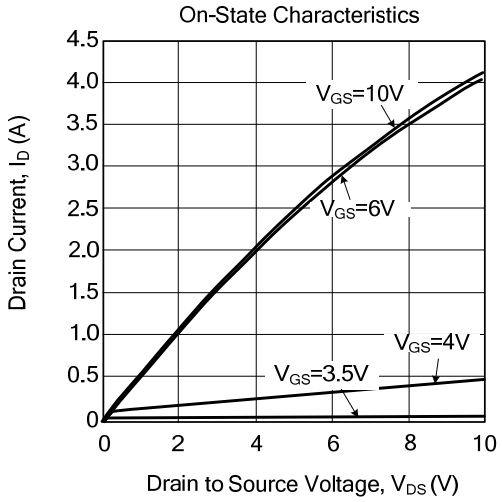
Unclamped Inductive Switching Waveforms

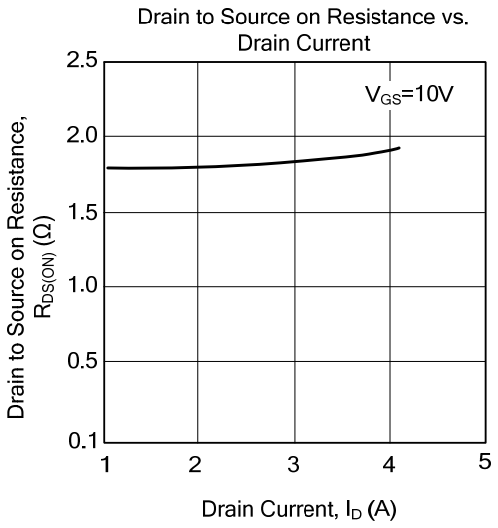
■ TYPICAL CHARACTERISTICS6

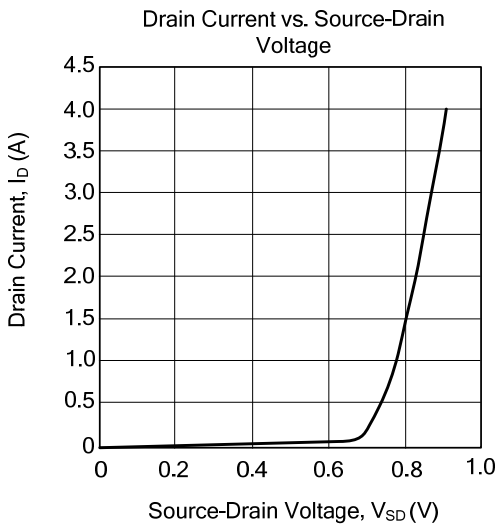






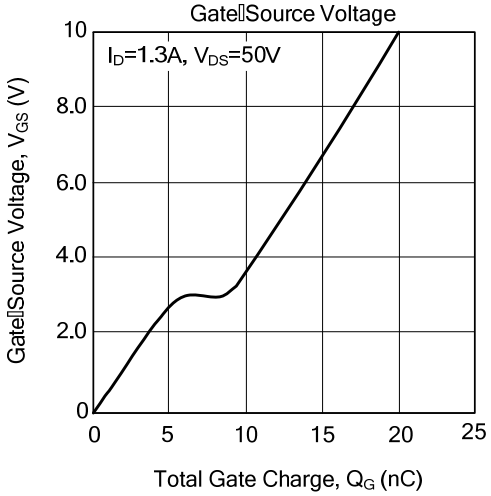




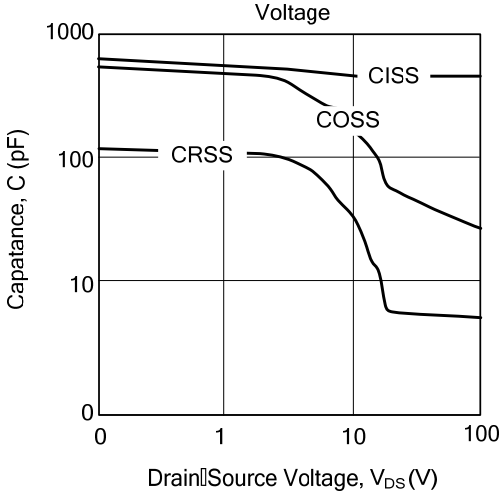


■ TYPICAL CHARACTERISTICS (Cont.)

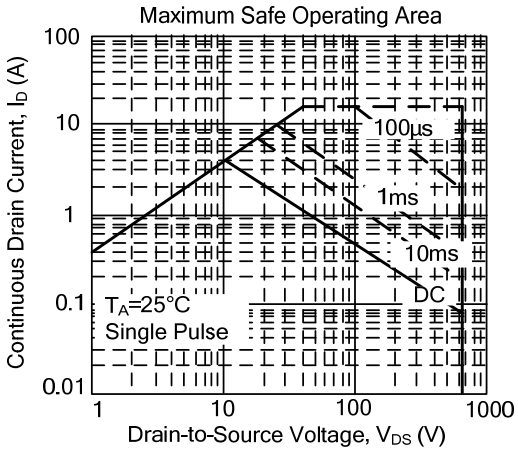
Typical Gate Charge vs. Gate-Source Voltage



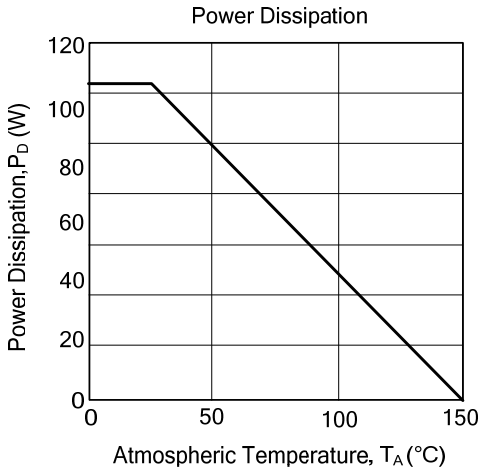
Typical Capatance vs Drain-Source Voltage



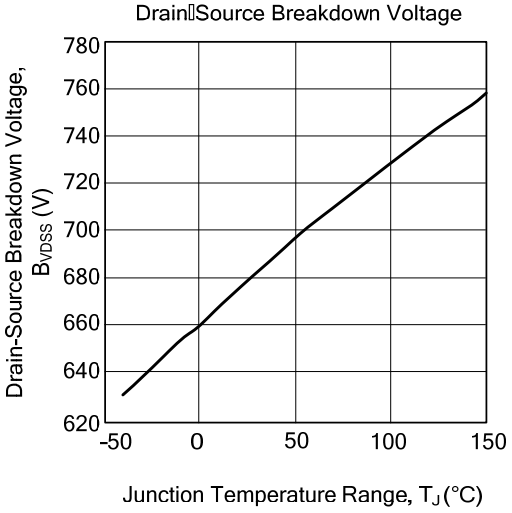
Maximum Safe Operating Area



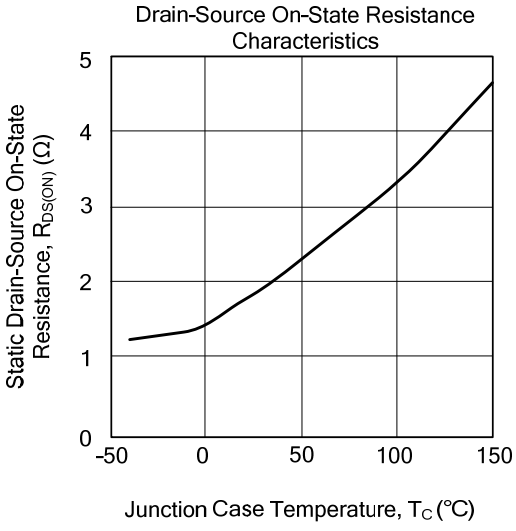
Power Dissipation



Drain-Source Breakdown Voltage



Drain-Source On-State Resistance Characteristics



■ TYPICAL CHARACTERISTICS (Cont.)